

**LISTING OF CLAIMS:**

The following listing of claims replaces all previous versions, and listings of claims in the present application.

66. (Currently amended) A semiconductor device comprising:

a semiconductor chip comprising a bump disposed on the semiconductor chip for being bonded to a control terminal, the bump formed resin, the control terminal securely bonded to the semiconductor chip using only the bump;

first and second radiation members thermally and electrically connected to the semiconductor chip interposed therebetween, and having a radiation surface for radiating heat from the semiconductor chip; and

first and second bonding members respectively interposed between the first radiation member and the semiconductor chip and between the semiconductor chip and the second radiation member, wherein:

the first and second radiation members are made of a metallic material that is superior to tungsten and molybdenum in at least one of an electrical conductivity and a thermal conductivity.

67. (Previously presented) The semiconductor device of claim 66, wherein no wire is required to be bonded from the control terminal to the semiconductor chip for providing electrical communication with an external device.

68. (New) A semiconductor device comprising:

a semiconductor chip having a bump disposed thereon, the bump formed of conductive resin, the bump for providing a secure bond between the semiconductor chip and a control terminal;

a pair of radiation members thermally and electrically connected to the semiconductor chip, the semiconductor chip interposed therebetween, the pair of radiation members having a radiation surface for radiating heat from the semiconductor chip and having conductive members protruding therefrom in a direction perpendicular to the radiation surface, the conductive members preventing parasitic inductance; and

first and second bonding members respectively interposed between the first radiation member and the semiconductor chip and between the semiconductor chip and the second radiation member.

69. (New) The semiconductor device of claim 68, wherein the first and second radiation members are made of a metallic material that is superior to tungsten and molybdenum in at least one of an electrical conductivity and a thermal conductivity.

70. (New) The semiconductor device of claim 68, wherein no wire is bonded from the control terminal to the semiconductor chip for providing electrical communication with an external device.